METHOD FOR PRODUCING PARTIAL SOI STRUCTURES COMPRISING ZONES CONNECTING A SUPERFICIAL LAYER AND A SUBSTRATE

ABSTRACT

The invention relates to a method for producing a semiconductor structure comprising a superficial layer (20'), at least one embedded layer (36, 46), and a support (30), which method comprises: a step of forming, on a first support, patterns (23) in a first material, a step of forming a semiconductor layer, between and on said patterns, a step of assembling said semiconductor layer with a second support (30).

(Fig. 2F)